

Wireless Power Transistor

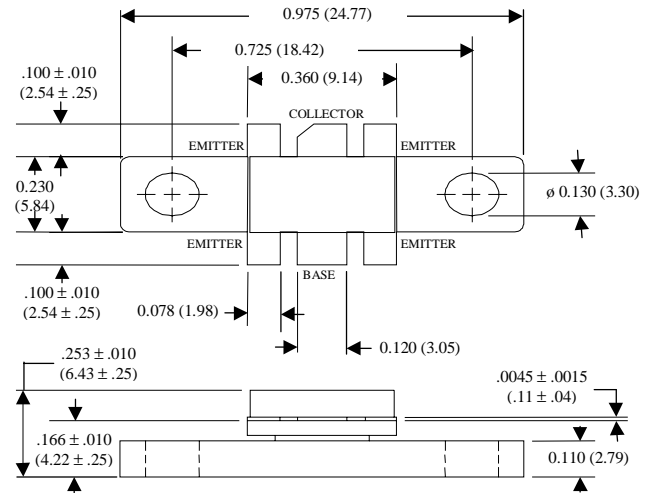
15 Watts, 850 - 960 MHz



Features

- Designed for Linear Amplifier Applications
- Class AB: -30 dBc Typ 3rd IMD at 15 Watts PEP
- Common Emitter Configuration
- Internal Input Impedance Matching
- Diffused Emitter Ballasting

Outline Drawing¹

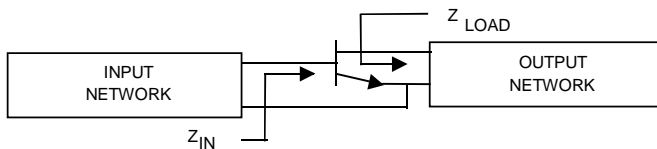


Notes: (unless otherwise specified)

1. Tolerances are: inches $\pm .005$ " (millimeters ± 0.13 mm)

Absolute Maximum Rating at 25°C

| Parameter | Symbol | Rating | Units |
|---------------------------|---------------|-------------|-------|
| Collector-Base Voltage | V_{CBO} | 60 | V |
| Collector-Emitter Voltage | V_{CES} | 60 | V |
| Emitter-Base Voltage | V_{EBO} | 3.0 | V |
| Collector Current | I_C | 1.8 | A |
| Dissipation @ 25°C | P_D | 43 | W |
| Storage Temperature | T_{stg} | -55 to +150 | °C |
| Junction Temperature | T_j | 200 | °C |
| Thermal Resistance | θ_{jc} | 3.5 | °C/W |



Typical Optimum Device Impedance

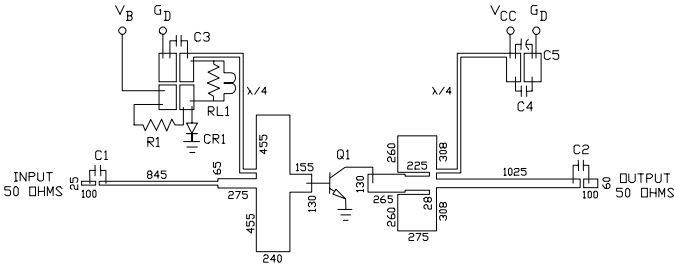
| F (MHz) | $Z_{in} (\Omega)$ | $Z_{load} (\Omega)$ |
|---------|-------------------|---------------------|
| 850 | $2.5 + j3.6$ | $4.3 + j2.6$ |
| 900 | $2.9 + j2.4$ | $4.4 + j3.4$ |
| 960 | $1.5 + j2.0$ | $4.3 + j3.9$ |

Electrical Specifications at 25°C

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|------------------|-----------------------------|---|-----|------|-------|
| BV_{CES} | Collector-Emitter Breakdown | $I_C=15$ mA | 60 | - | V |
| I_{CES} | Collector-Emitter Leakage | $V_{CE}=24.0$ V | - | 2.0 | mA |
| BV_{CEO} | Collector-Emitter Breakdown | $I_C=40$ mA | 24 | - | V |
| BV_{EBO} | Emitter-Base Breakdown | $I_B=2.5$ mA | 3.0 | - | V |
| h_{FE} | DC Forward Current Gain | $V_{CE}=5.0$ V, $I_C=0.5$ A | 15 | 120 | - |
| G_P | Power Gain | $V_{CC}=24$ V, $I_{CQ}=100$ mA, $P_{out}=15$ W, $f=900$ MHz | 12 | - | dB |
| η | Collector Efficiency | $V_{CC}=24$ V, $I_{CQ}=100$ mA, $P_{out}=15$ W, $f=900$ MHz | 50 | - | % |
| R_L | Input Return Loss | $V_{CC}=24$ V, $I_{CQ}=100$ mA, $P_{out}=15$ W, $f=900$ MHz | 10 | - | dB |
| VSWR | Load Mismatch Tolerance | $V_{CC}=24$ V, $I_{CQ}=100$ mA, $P_{out}=15$ W PEP, $f=900$ MHz, $\Delta f=100$ kHz | - | 10:1 | - |
| IMD ₃ | 3rd Order IMD | $V_{CC}=24$ V, $I_{CQ}=100$ mA, $P_{out}=15$ W PEP, $f=900$ MHz, $\Delta f=100$ kHz | - | -30 | dBc |

V2.00

Electrical Schematic¹



Notes:

- 1. Dimensions are in mils.

Electrical Schematic Parts List

| | |
|------------|--|
| C1, C2, C3 | 100 pF ATC Size A |
| C4 | 5000 pF ATC Size B |
| C5 | 50 uF 50 Volts |
| CR1 | Diode cathode tied to flange (Harris 1N4245) |
| Q1 | PH0810-15 |
| R1 | 5 Ohms ¼ W |
| RL1 | 10T / No. 22 AWG on 3.1 Ohm ¼ Watt |
| Board Type | Rogers 6010.5 .025" thick, E _R = 10.5 |